

General Purpose Transistors

NPN Silicon

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

MAXIMUM RATINGS

Rating	Symbol	2222	2222A	Unit
Collector-Emitter Voltage	V_{CEO}	30	40	Vdc
Collector-Base Voltage	V_{CBO}	60	75	Vdc
Emitter-Base Voltage	V_{EBO}	5.0	6.0	Vdc
Collector Current — Continuous	I_C	600	600	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1)	P_D	225	mW
$T_A = 25^\circ\text{C}$			
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	R_{JJA}	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation	P_D	300	mW
Alumina Substrate, (2) $T_A = 25^\circ\text{C}$			
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	R_{JJA}	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING

LMBT2222LT1 = M1B; LMBT2222ALT1 = 1P

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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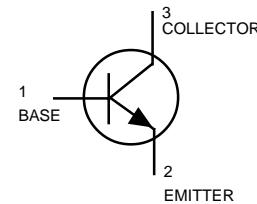
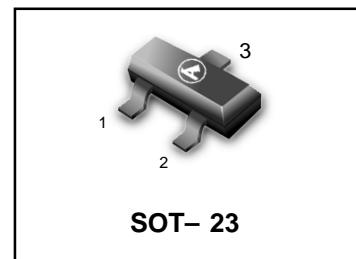
OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	LMBT2222 LMBT2222A	$V_{(BR)CEO}$	30 40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}, I_E = 0$)	LMBT2222 LMBT2222A	$V_{(BR)CBO}$	60 75	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}, I_C = 0$)	LMBT2222 LMBT2222A	$V_{(BR)EBO}$	5.0 6.0	—	Vdc
Collector Cutoff Current ($V_{CE} = 60 \text{ Vdc}, I_{EB(off)} = 3.0 \text{ Vdc}$)	LMBT2222A	I_{CEX}	—	10	nAdc
Collector Cutoff Current ($V_{CB} = 50 \text{ Vdc}, I_E = 0$)	LMBT2222	I_{CBO}	—	0.01	μAdc
($V_{CB} = 60 \text{ Vdc}, I_E = 0$)	LMBT2222A		—	0.01	
($V_{CB} = 50 \text{ Vdc}, I_E = 0, T_A = 125^\circ\text{C}$)	LMBT2222		—	10	
($V_{CB} = 60 \text{ Vdc}, I_E = 0, T_A = 125^\circ\text{C}$)	LMBT2222A		—	10	
Emitter Cutoff Current ($V_{EB} = 3.0 \text{ Vdc}, I_C = 0$)	LMBT2222A	I_{EBO}	—	100	nAdc
Base Cutoff Current ($V_{CE} = 60 \text{ Vdc}, V_{EB(off)} = 3.0 \text{ Vdc}$)	LMBT2222A	I_{BL}	—	20	nAdc

1. FR-5 = $1.0 \times 0.75 \times 0.062$ in.

2. Alumina = $0.4 \times 0.3 \times 0.024$ in. 99.5% alumina.

LMBT2222LT1
LMBT2222ALT1



ORDERING INFORMATION

Device	Package	Shipping
LMBT2222LT1	SOT-23	3000/Tape & Reel
LMBT2222LT1G	SOT-23	3000/Tape & Reel
LMBT2222ALT1	SOT-23	3000/Tape & Reel
LMBT2222ALT1G	SOT-23	3000/Tape & Reel

LMBT2222LT1 LMBT2222ALT1
ELECTRICAL CHARACTERISTICS (T A = 25°C unless otherwise noted) (Continued)

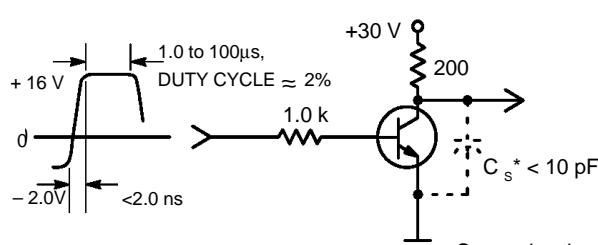
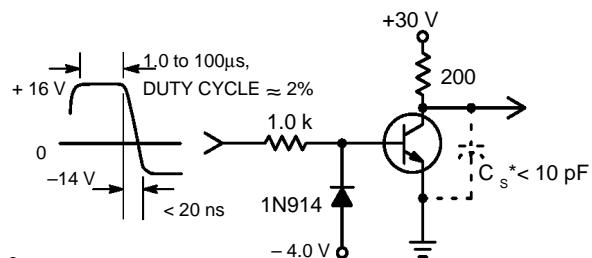
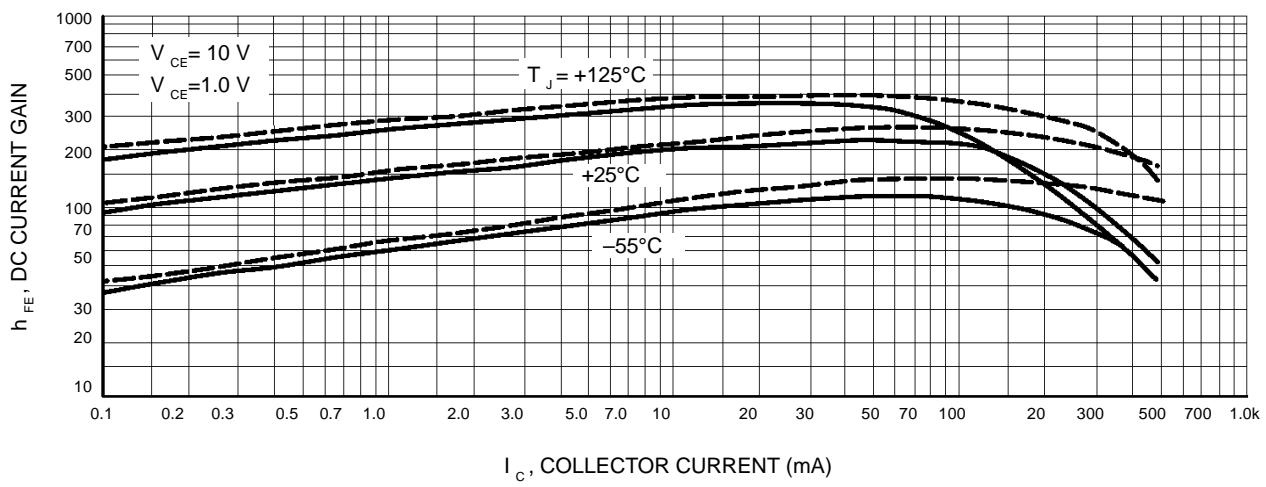
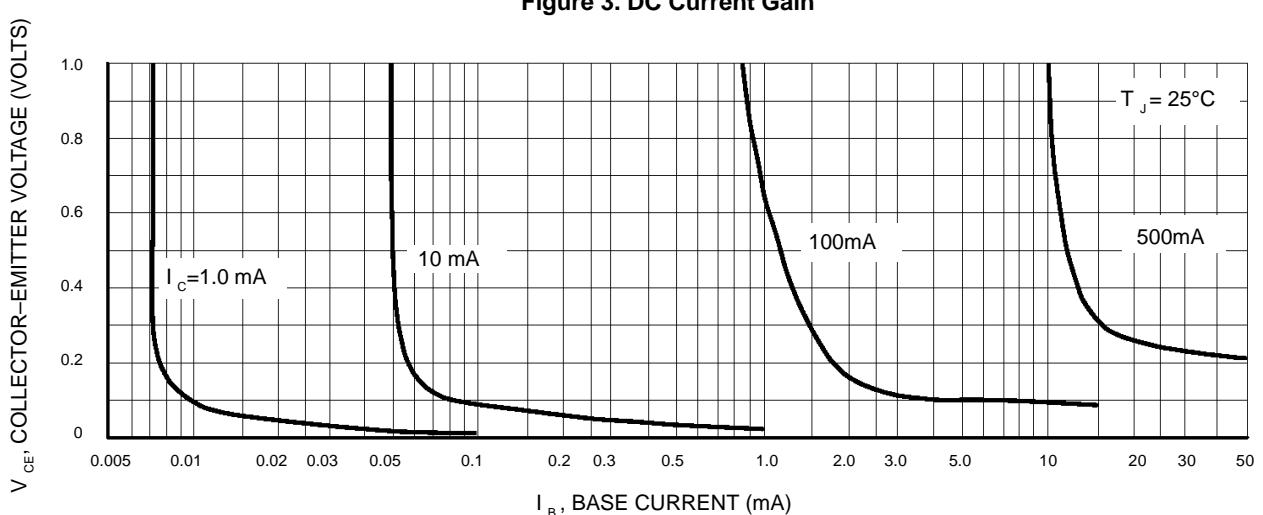
Characteristic	Symbol	Min	Max	Unit	
ON CHARACTERISTICS					
DC Current Gain (I C = 0.1 mAdc, V CE = 10 Vdc)	h FE	—	—	—	
(I C = 1.0 mAdc, V CE = 10 Vdc)		35	—	—	
(I C = 10 mAdc, V CE = 10 Vdc)		50	—	—	
(I C = 10 mAdc, V CE = 10 Vdc, T A = -55°C)	LMBT2222A only	75	—	—	
(I C = 150 mAdc, V CE = 10 Vdc) (3)		35	—	—	
(I C = 150 mAdc, V CE = 1.0 Vdc) (3)		100	300	—	
(I C = 150 mAdc, V CE = 1.0 Vdc) (3)	LMBT2222	50	—	—	
(I C = 500 mAdc, V CE = 10 Vdc) (3)	LMBT2222A	30	—	—	
		40	—	—	
Collector-Emitter Saturation Voltage(3)	V CE(sat)			Vdc	
(I C = 150 mAdc, I B = 15 mAdc)	LMBT2222	—	0.4	—	
	LMBT2222A	—	0.3	—	
(I C = 500mAdc, I B = 50 mAdc)	LMBT2222	—	1.6	—	
	LMBT2222A	—	1.0	—	
Base-Emitter Saturation Voltage	V BE(sat)			Vdc	
(I C = 150 mAdc, I B = 15 mAdc)	LMBT2222	—	1.3	—	
	LMBT2222A	0.6	1.2	—	
(I C = 500 mAdc, I B = 50 mAdc)	LMBT2222	—	2.6	—	
	LMBT2222A	—	2.0	—	
SMALL-SIGNAL CHARACTERISTICS					
Current-Gain — Bandwidth Product(4)	LMBT2222	f T	250	—	MHz
(I C = 20mA, V CE= 20Vdc, f = 100MHz)	LMBT2222A		300	—	—
Output Capacitance(V CB = 10 Vdc, I E = 0, f = 1.0 MHz)	C obo	—	8.0	pF	
Input Capacitance (V EB = 0.5 Vdc, I C = 0, f = 1.0 MHz)	LMBT2222	C ibo	—	30	pF
	LMBT2222A	—	25	—	—
Input Impedance(V CE = 10 Vdc, I C = 1.0 mA, f = 1.0 kHz)	LMBT2222A	h ie	2.0	8.0	kΩ
(V CE = 10 Vdc, I C = 10 mA, f = 1.0 kHz)	LMBT2222A		0.25	1.25	—
Voltage Feedback Ratio(V CE=10 Vdc, I C= 1.0mA, f=1.0kHz)	LMBT2222A	h re	—	8.0	X 10 ⁻⁴
(V CE= 10 Vdc, I C = 10 mA, f = 1.0 kHz)	LMBT2222A		—	4.0	—
Small-Signal Current Gain(V CE=10Vdc,I C=1.0mA,f=1.0kHz)	LMBT2222A	h fe	50	300	—
(V CE= 10 Vdc, I C = 10 mA, f = 1.0 kHz)	LMBT2222A		75	375	—
Output Admittance(V CE= 10 Vdc, I C = 1.0 mA, f = 1.0 kHz)	LMBT2222A	h oe	5.0	35	μmhos
(V CE= 10 Vdc, I C = 10 mA, f = 1.0 kHz)	LMBT2222A		25	200	—
Current Base Time Constant (V CB= 20 Vdc, I E = 20 mA, f = 31.8 MHz)	LMBT2222A	rb, C c	—	150	ps
Noise Figure(V CE=10Vdc, I C=100μA, R S=1.0kΩ, f =1.0kHz)	LMBT2222A	NF	—	4.0	dB

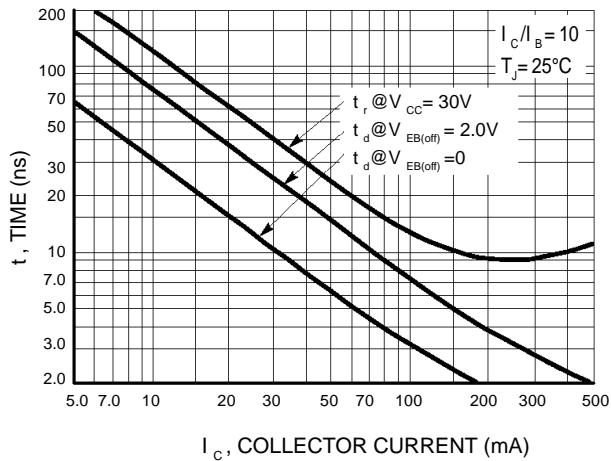
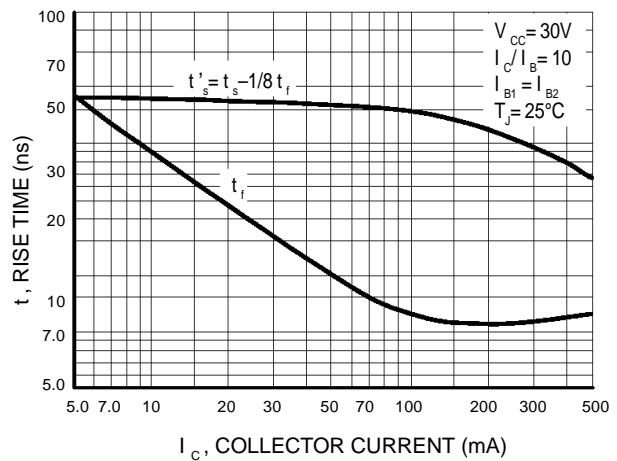
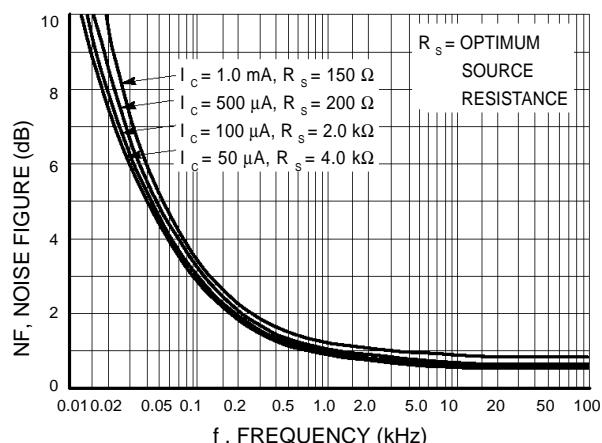
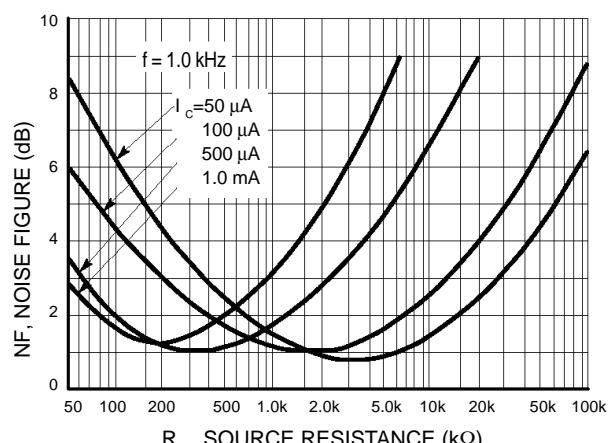
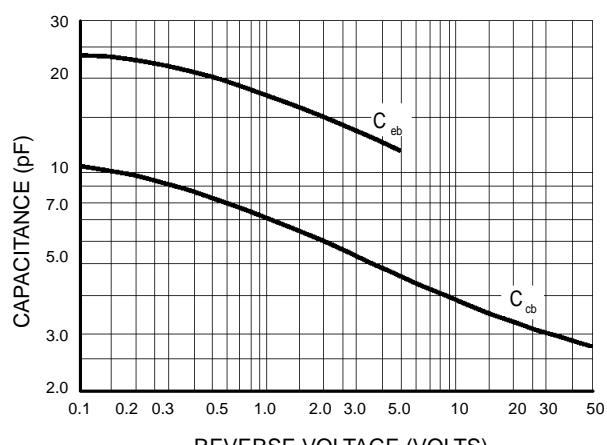
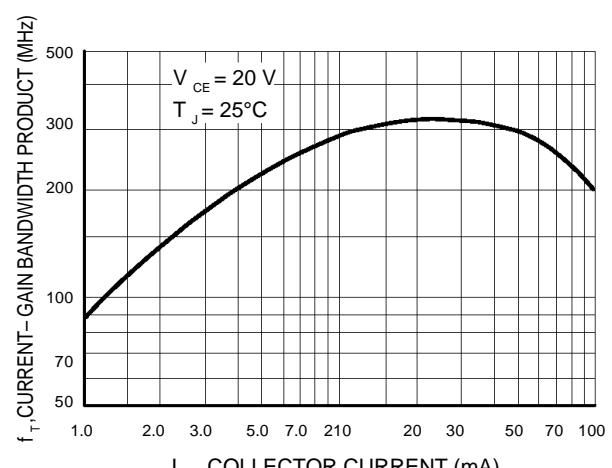
SWITCHING CHARACTERISTICS

Delay Time	(V CC = 30 Vdc, V EB(off) = - 0.5 Vdc)	t d	—	10	ns
Rise Time	I C = 150 mA, I B1 = 15 mA	t r	—	25	
Storage Time	(V CC = 30 Vdc, I C = 150 mA)	t s	—	225	ns
Fall Time	I B1 = I B2 = 15 mA	t f	—	60	

3. Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.

4. f_T is defined as the frequency at which $|h_{fe}|$ extrapolates to unity.

LMBT2222LT1 LMBT2222ALT1
SWITCHING TIME EQUIVALENT TEST CIRCUITS

Figure 1. Turn-On Time

Figure 2. Turn-Off Time

Figure 3. DC Current Gain

Figure 4. Collector Saturation Region

LMBT2222LT1 LMBT2222ALT1

Figure 5. Turn-On Time

Figure 6. Turn - Off Time

Figure 7. Frequency Effects

Figure 8. Source Resistance Effects

Figure 9. Capacitance

Figure 10. Current-Gain Bandwidth Product

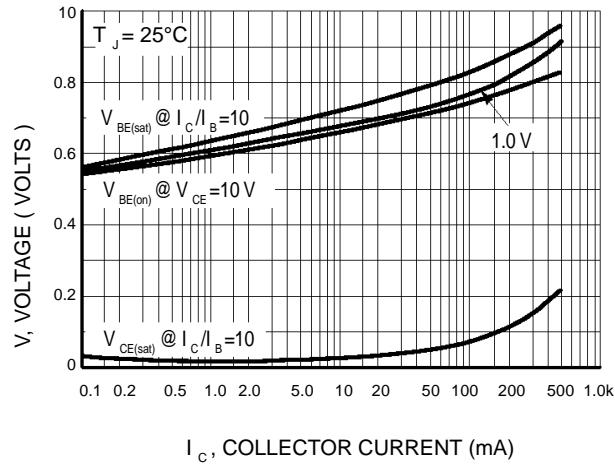
LMBT2222LT1 LMBT2222ALT1


Figure 11. "On" Voltages

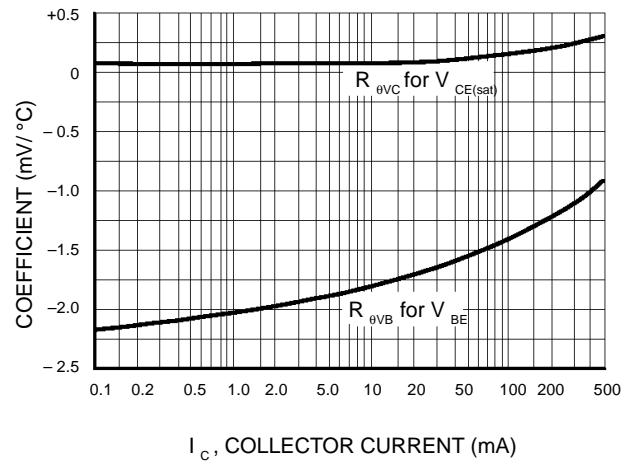


Figure 12. Temperature Coefficients